

Kingtronics®

KT2N60

N-Channel Power MOSFET

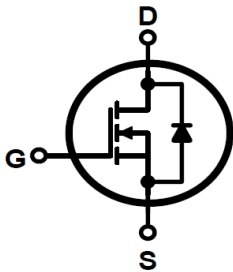
FEATURES

LOW ON-RESISTANCE
 FAST SWITCHING
 HIGH INPUT RESISTANCE
 ROHS COMPLIANT

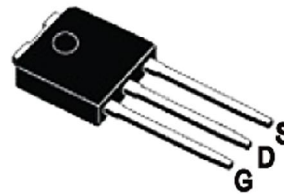
PRODUCT SUMMARY

V_{DS}	600	V
I_D	2.0	A
$P_D(T_C=25^\circ\text{C})$	25	W
$R_{DS(ON)typ}$	3.5	Ω

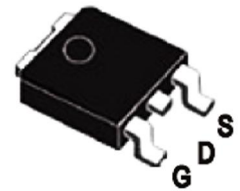
Schematic Diagram (N-Channel)



TO-251



TO-252



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

$T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Rating	Units
V_{DS}	Drain-source Voltage	600	V
I_D	Continuous Drain Current $T_C=25^\circ\text{C}$	2.0*	A
	Continuous Drain Current $T_C = 100^\circ\text{C}$	1.2*	A
V_{GS}	Gate-Source Voltage	± 30	V
I_{DM}	Drain Current-Pulsed (1)	8.0*	A
P_D	Power Dissipation	25	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55-150	$^\circ\text{C}$
EAS	Single Pulse Avalanche Energy (2)	28	mJ

*Drain current limited by maximum junction temperature

(1) Repetitive rating: Pulse width limited by maximum junction temperature

(2) Starting $T_j=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $L=10\text{mH}$, $R_G=25\Omega$, $I_{AS}=2.0\text{A}$

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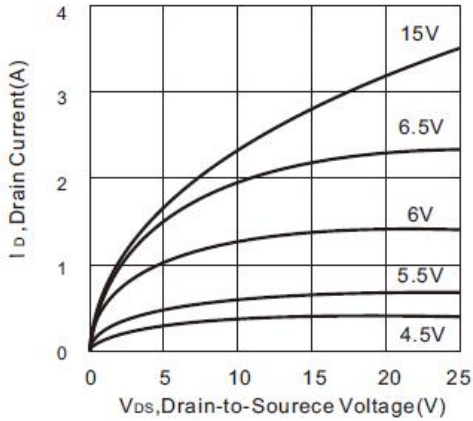
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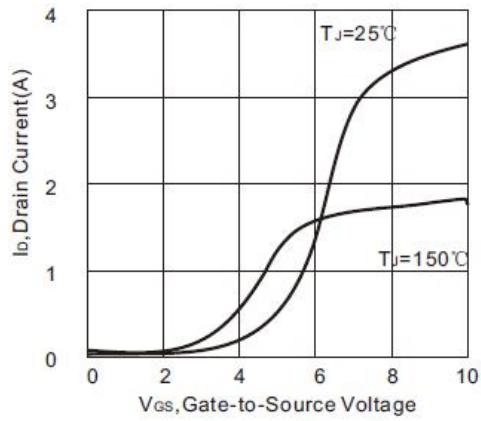
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RATING AND CHARACTERISTIC CURVES

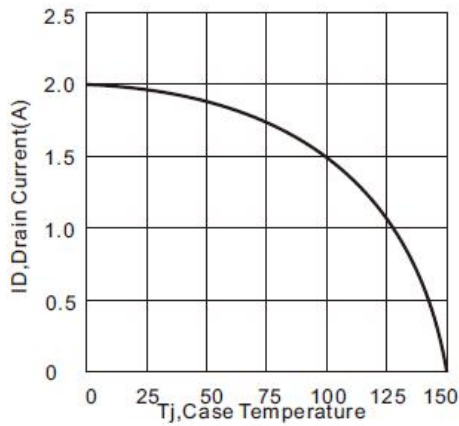
Output Characteristics



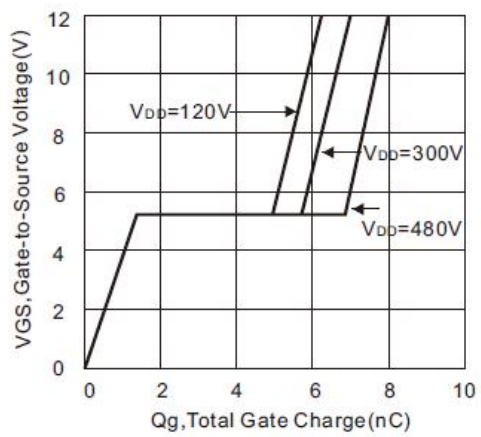
Transfer Characteristics



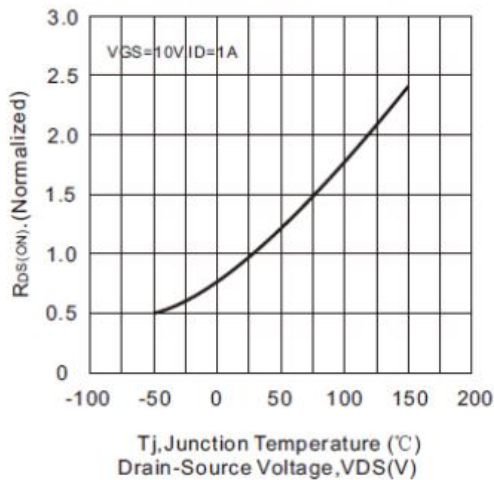
Drain Current VS. Temperature



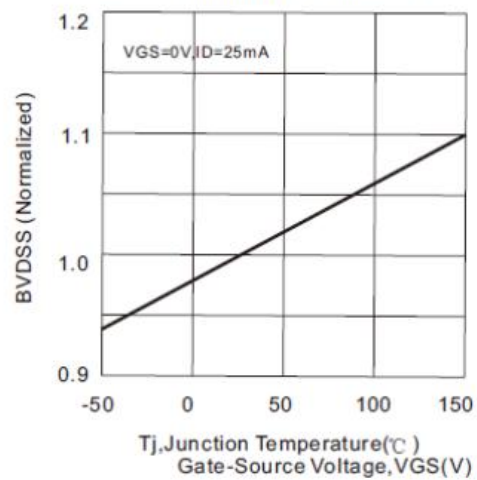
Gate Charge



On-Resistance vs. Junction Temperature



BVDS Variation VS. Temperature

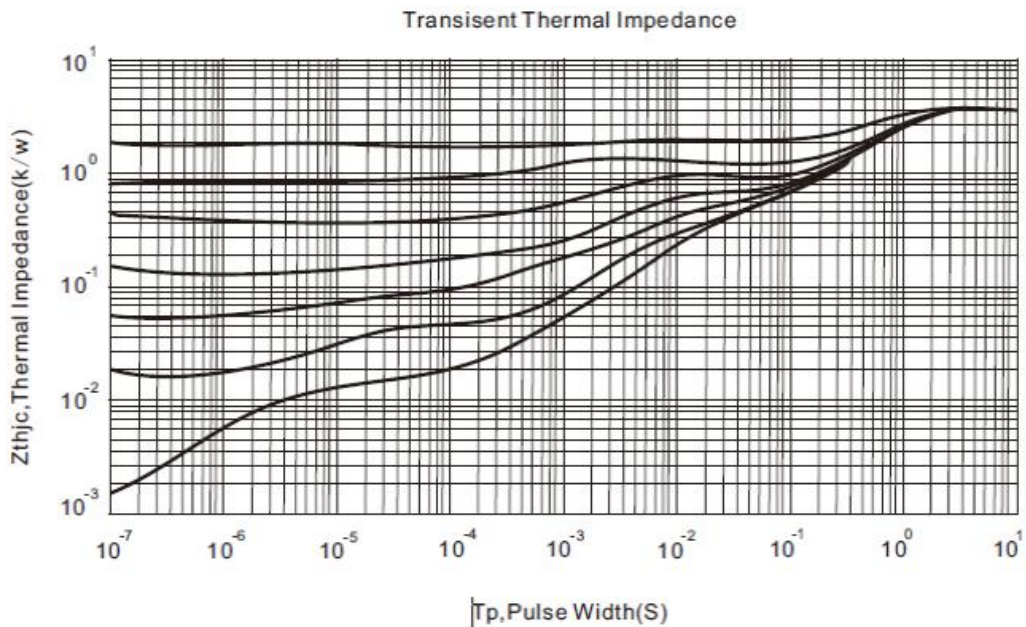
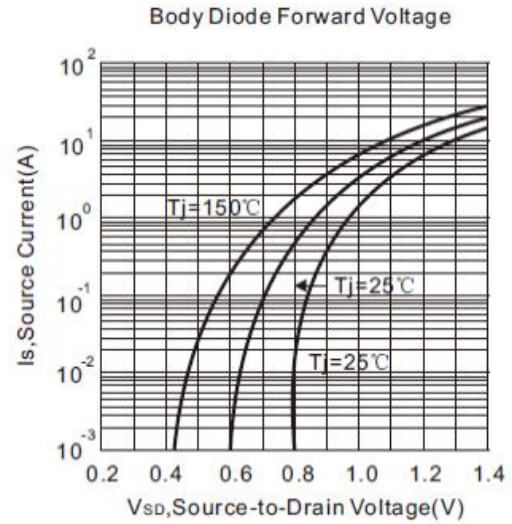
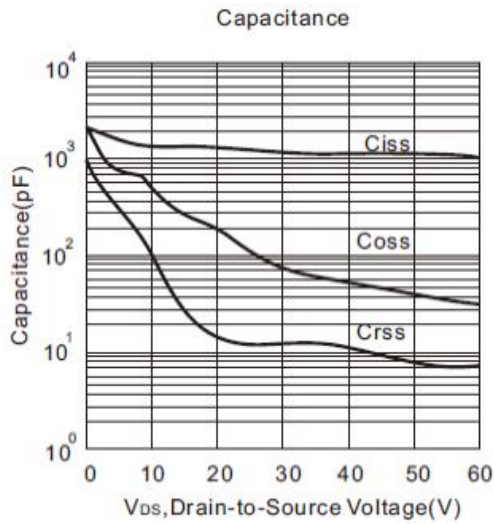


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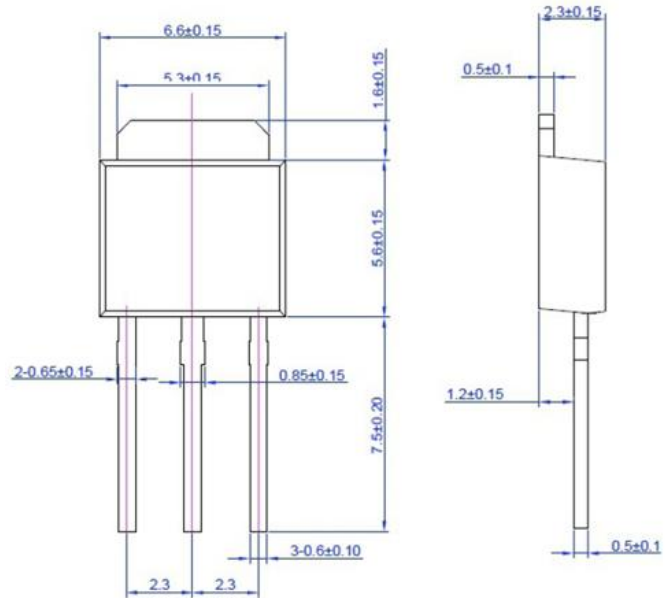
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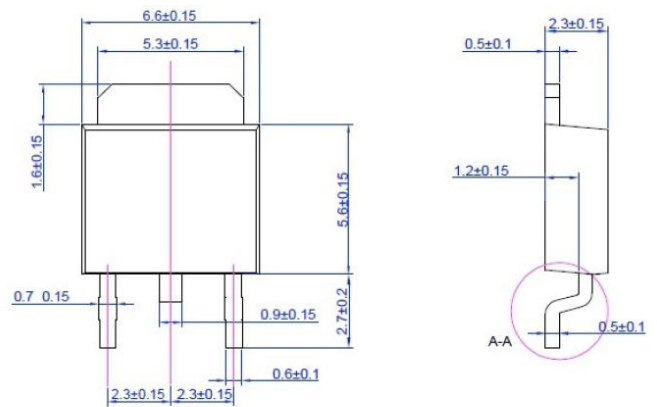
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Package Dimensions

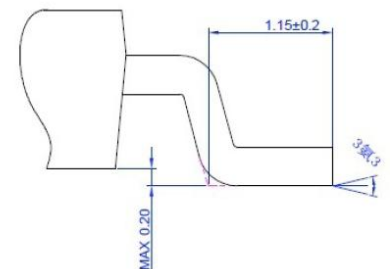
TO-251



TO-252



A-A



Notes: Specifications are subject to change without notice.

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